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Development of silicon microstrip sensors in 150 mm p-type wafers

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We have fabricated silicon microstrip sensors in 150 mm p-type wafers and carried out irradiation of protons of 70 MeV up to 2x10ˆ15 1-MeV neutron equivalent/cmˆ2. Full depletion votages along the fluence of the protons of 70 MeV have shown quite different development than those in 100 mm p-type wafers. The sensors are made of different isolation structures in the n-strip side. Characterization of the isolation structures are also made for the onset voltages of microdischarge, isolation of the n-strips, etc.

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